



# N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
30	0.034 at V <sub>GS</sub> = 4.5 V	6.1			
	0.050 at V <sub>GS</sub> = 2.5 V	5.0			

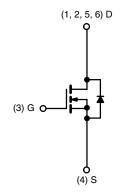
# **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 2.5 V Rating for 30 V N-Channel
- Low R<sub>DS(on)</sub> for Footprint Area Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

• Li-Ion Battery Protection



N-Channel MOSFET

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Ordering Information: Si3434DV-T1-E3 (Lead (Pb)-free)

Si3434DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATINGS</b>	Γ <sub>A</sub> = 25 °C, unle	ss otherwise r	noted			
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30		V	
Gate-Source Voltage		V <sub>GS</sub>	± 12		V	
Continuous Drain Current /T 150 °C\8	T <sub>A</sub> = 25 °C	I <sub>D</sub>	6.1	4.6	۸	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		4.9	3.6		
Pulsed Drain Current		I <sub>DM</sub>	30		Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.7	1.0		
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.0 1.14		W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	] <sup>P</sup> D	1.3	0.73	]	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana landia la Andria d	t ≤ 5 s	R <sub>thJA</sub>	40	62.5	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' ¹thJA	90	110	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	25	30	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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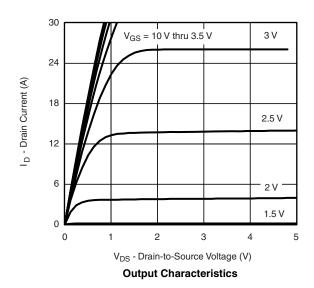
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Test Conditions Min.		Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$	0.6			٧		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA		
Zoro Coto Voltago Droin Current		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V		1			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			5	μΑ		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α		
Drain-Source On-State Resistance <sup>a</sup>	В	$V_{GS} = 4.5 \text{ V}, I_D = 6.1 \text{ A}$		0.028	0.034	0		
	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 2 \text{ A}$		0.042	0.050	Ω		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.1 A		20		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V		0.8	1.2	٧		
Dynamic <sup>b</sup>			•		•			
Total Gate Charge	$Q_g$			8	12			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.1 \text{ A}$		1.9		nC		
Gate-Drain Charge	$Q_{gd}$			2.6				
Turn-On Delay Time	t <sub>d(on)</sub>			21	40			
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		45	90			
Turn-Off Delay Time	t <sub>d(off)</sub>	$t_{d(off)}$ $I_D \cong 1 \text{ A, } V_{GEN} = 4.5 \text{ V, } R_g = 6 \Omega$		40	80	ns		
Fall Time	t <sub>f</sub>			30	60			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.7 A, dI/dt = 100 A/μs		40	80			

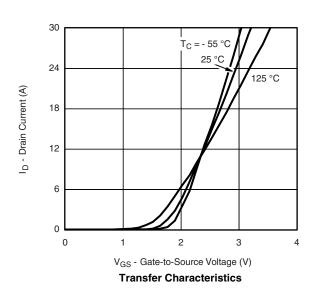
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



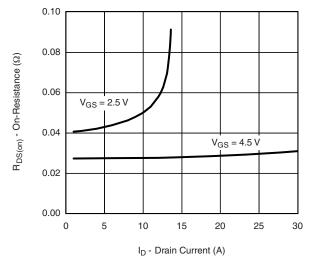




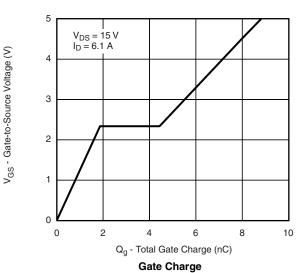


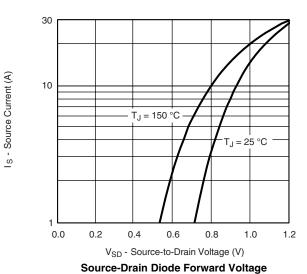


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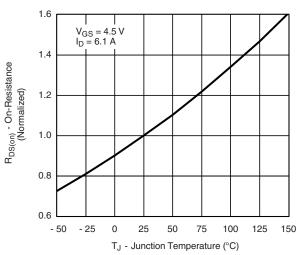


#### On-Resistance vs. Drain Current

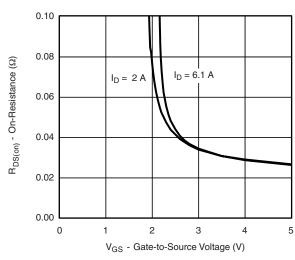




1200 1000  $\mathsf{C}_{\mathsf{iss}}$ C - Capacitance (pF) 800 600 400 Coss 200 0 0 5 10 15 20 25 30



On-Resistance vs. Junction Temperature

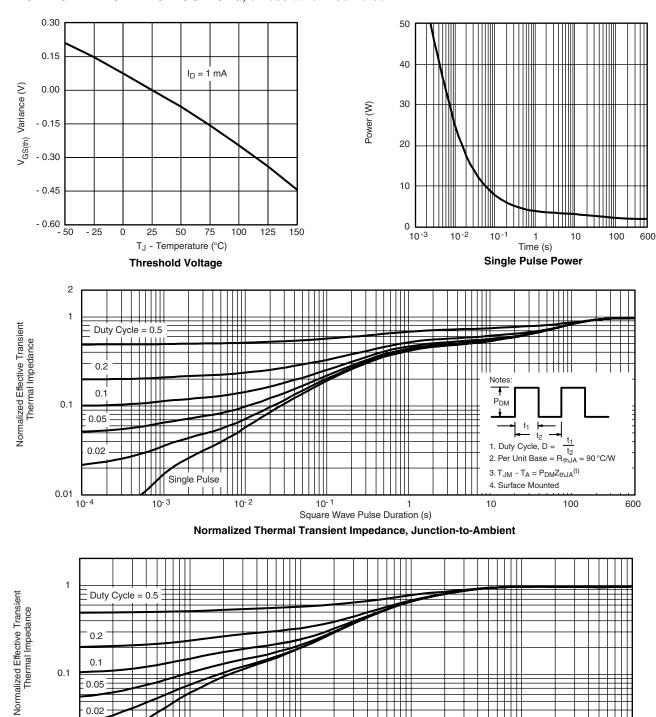


On-Resistance vs. Gate-to-Source Voltage

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71610">www.vishay.com/ppg?71610</a>.

0.01

Single Pulse

10-3

10



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